

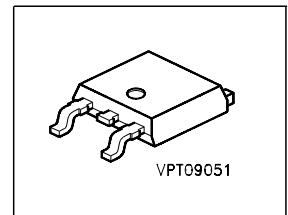
Fast Switching EmCon Diode

Feature

- 600 V EmCon technology
- Fast recovery
- Soft switching
- Low reverse recovery charge
- Low forward voltage
- 175°C operating temperature
- Easy paralleling

Product Summary

V_{RRM}	600	V
I_F	9	A
V_F	1.5	V
T_{jmax}	175	°C



Type	Package	Ordering Code	Marking	Pin 1	PIN 2	PIN 3
IDD09E60	P-TO252-3-1	Q67040-S4379	D09E60	NC	C	A

Maximum Ratings, at $T_j = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Value	Unit
Repetitive peak reverse voltage	V_{RRM}	600	V
Continuous forward current $T_C=25^\circ\text{C}$ $T_C=90^\circ\text{C}$	I_F	19.3 13	A
Surge non repetitive forward current $T_C=25^\circ\text{C}$, $t_p=10$ ms, sine halfwave	I_{FSM}	40	
Maximum repetitive forward current $T_C=25^\circ\text{C}$, t_p limited by T_{jmax} , $D=0.5$	I_{FRM}	29.5	
Power dissipation $T_C=25^\circ\text{C}$ $T_C=90^\circ\text{C}$	P_{tot}	57.7 32.7	W
Operating and storage temperature	T_j , T_{stg}	-55...+175	°C
Soldering temperature for 10s (according to JEDEC J-STD-020A)	T_S	255	°C

Thermal Characteristics

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Characteristics					
Thermal resistance, junction - case	R_{thJC}	-	-	2.6	K/W
SMD version, device on PCB:	R_{thJA}				
@ min. footprint		-	-	75	
@ 6 cm ² cooling area 1)		-	-	50	

Electrical Characteristics, at $T_j = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Static Characteristics					
Reverse leakage current	I_R				μA
$V_R=600\text{V}$, $T_J=25^{\circ}\text{C}$		-	-	50	
$V_R=600\text{V}$, $T_J=150^{\circ}\text{C}$		-	-	750	
Forward voltage drop	V_F				V
$I_F=9\text{A}$, $T_J=25^{\circ}\text{C}$		-	1.5	2	
$I_F=9\text{A}$, $T_J=150^{\circ}\text{C}$		-	1.5	-	

¹⁾Device on 40mm*40mm*1.5mm epoxy PCB FR4 with 6cm² (one layer, 70 μm thick) copper area for drain connection. PCB is vertical without blown air.

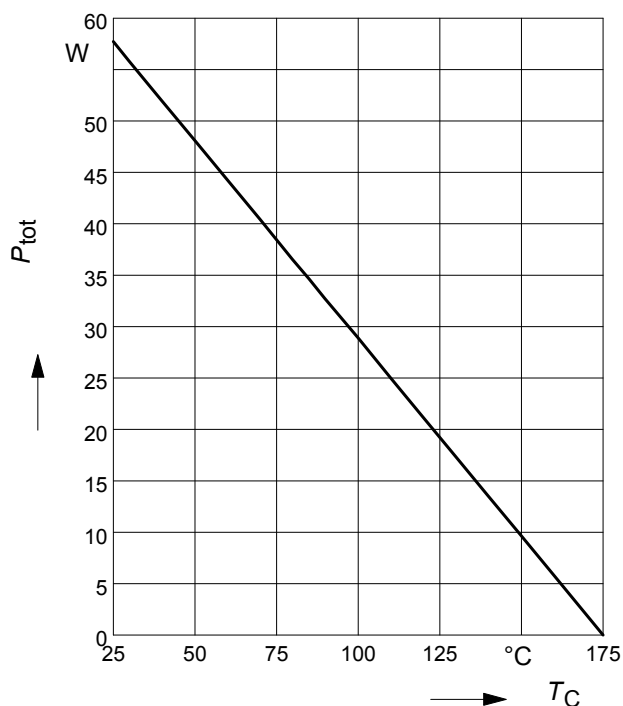
Electrical Characteristics, at $T_j = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Dynamic Characteristics					
Reverse recovery time $V_R=400V, I_F=9A, di_F/dt=800A/\mu s, T_j=25^{\circ}C$ $V_R=400V, I_F=9A, di_F/dt=800A/\mu s, T_j=125^{\circ}C$ $V_R=400V, I_F=9A, di_F/dt=800A/\mu s, T_j=150^{\circ}C$	t_{rr}	- - -	75 110 112	- - -	ns
Peak reverse current $V_R=400V, I_F=9A, di_F/dt=800A/\mu s, T_j=25^{\circ}C$ $V_R=400V, I_F=9A, di_F/dt=800A/\mu s, T_j=125^{\circ}C$ $V_R=400V, I_F=9A, di_F/dt=800A/\mu s, T_j=150^{\circ}C$	I_{rrm}	- - -	10.2 11.8 12.3	- - -	A
Reverse recovery charge $V_R=400V, I_F=9A, di_F/dt=800A/\mu s, T_j=25^{\circ}C$ $V_R=400V, I_F=9A, di_F/dt=800A/\mu s, T_j=125^{\circ}C$ $V_R=400V, I_F=9A, di_F/dt=800A/\mu s, T_j=150^{\circ}C$	Q_{rr}	- - -	343 585 612	- - -	nC
Reverse recovery softness factor $V_R=400V, I_F=9A, di_F/dt=800A/\mu s, T_j=25^{\circ}C$ $V_R=400V, I_F=9A, di_F/dt=800A/\mu s, T_j=125^{\circ}C$ $V_R=400V, I_F=9A, di_F/dt=800A/\mu s, T_j=150^{\circ}C$	S	- - -	4 5.5 5.7	- - -	

1 Power dissipation

$$P_{\text{tot}} = f(T_C)$$

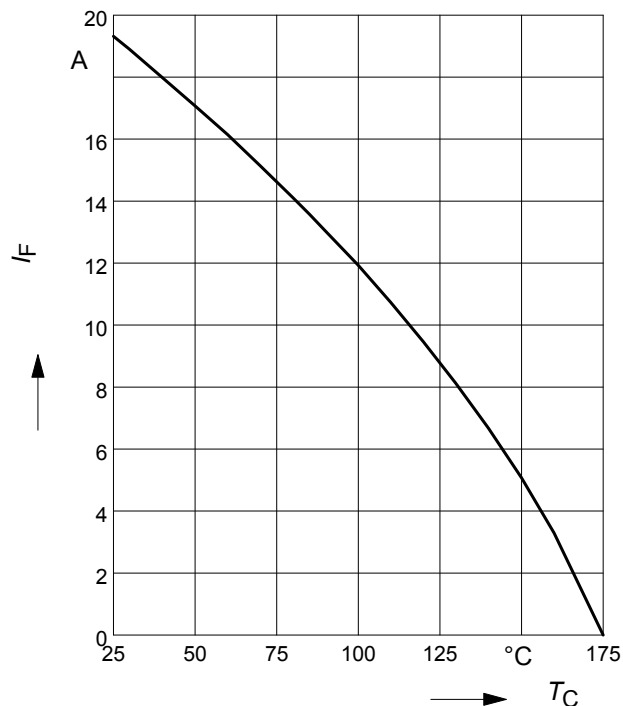
parameter: $T_j \leq 175^\circ\text{C}$



2 Diode forward current

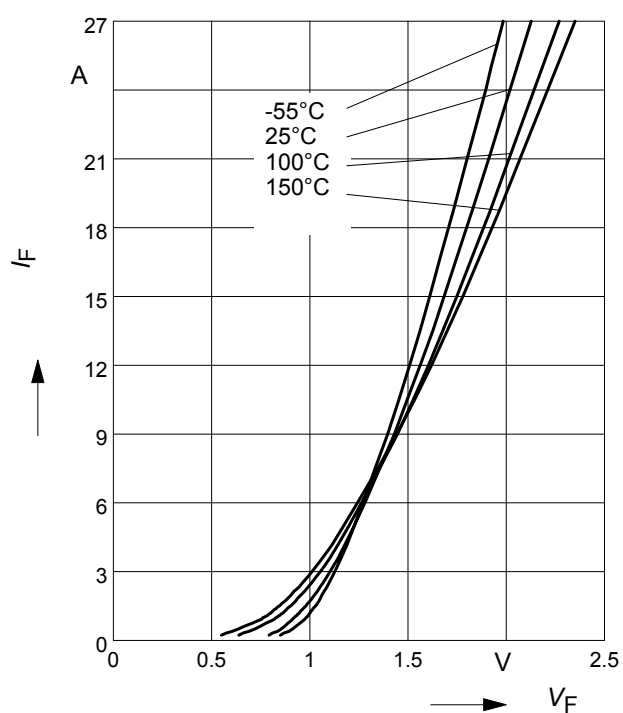
$$I_F = f(T_C)$$

parameter: $T_j \leq 175^\circ\text{C}$



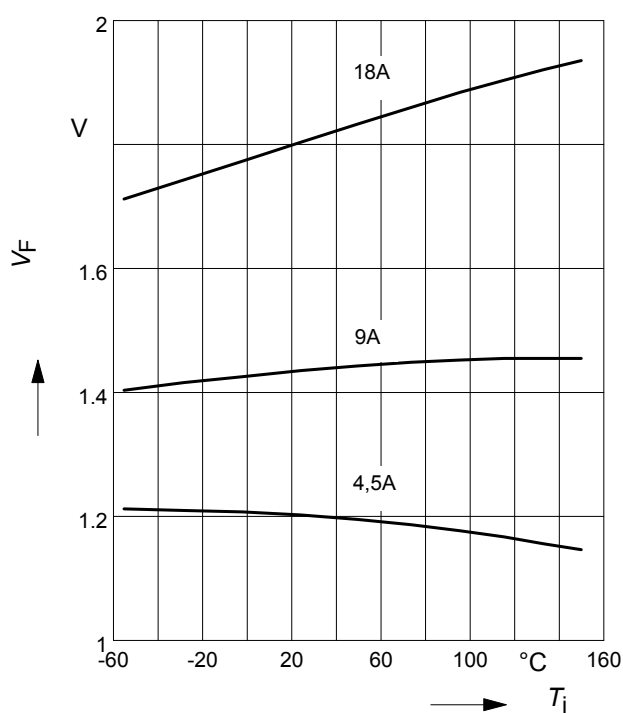
3 Typ. diode forward current

$$I_F = f(V_F)$$



4 Typ. diode forward voltage

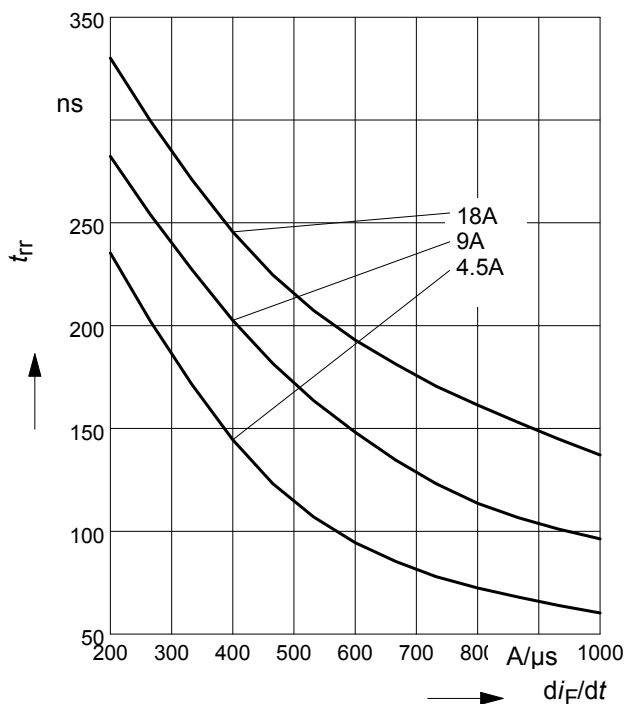
$$V_F = f(T_j)$$



5 Typ. reverse recovery time

$$t_{rr} = f(dI_F/dt)$$

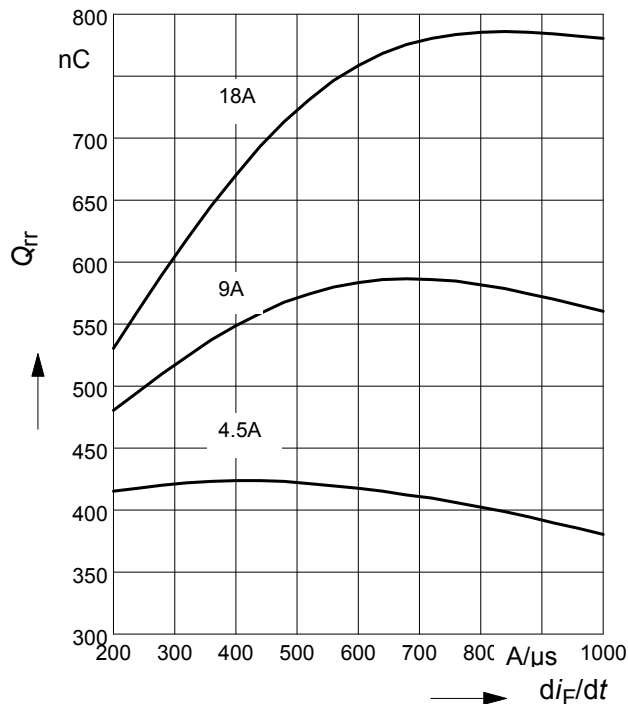
parameter: $V_R = 400V$, $T_j = 125^\circ C$



6 Typ. reverse recovery charge

$$Q_{rr} = f(dI_F/dt)$$

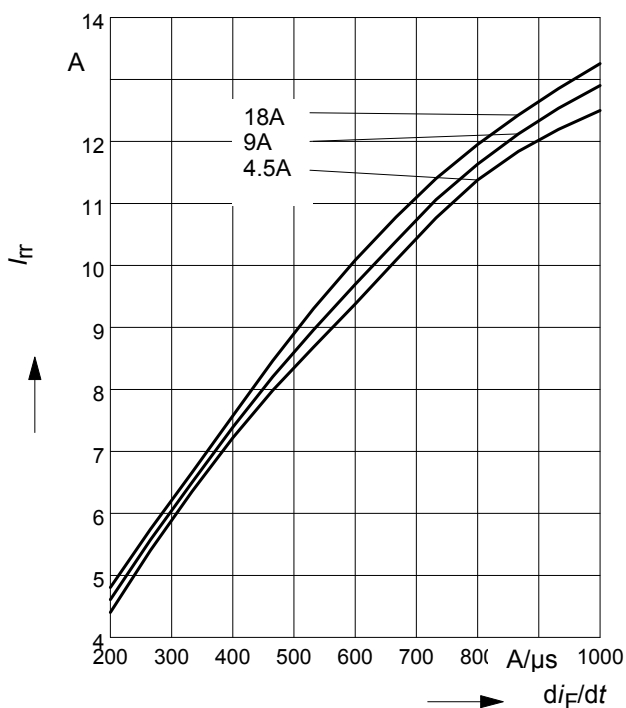
parameter: $V_R = 400V$, $T_j = 125^\circ C$



7 Typ. reverse recovery current

$$I_{rr} = f(dI_F/dt)$$

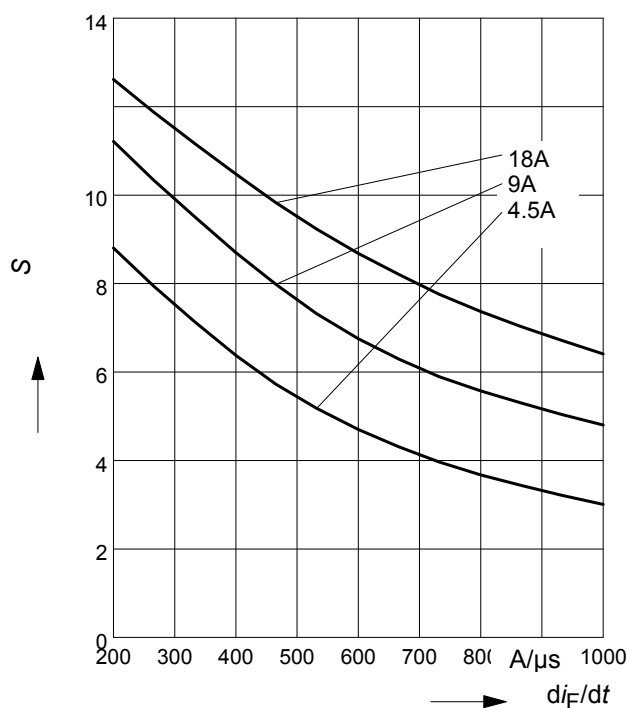
parameter: $V_R = 400V$, $T_j = 125^\circ C$



8 Typ. reverse recovery softness factor

$$S = f(dI_F/dt)$$

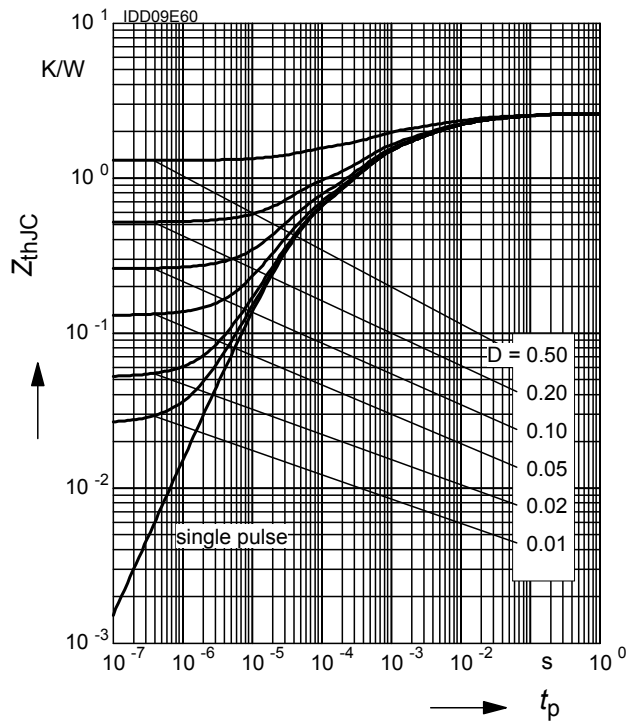
parameter: $V_R = 400V$, $T_j = 125^\circ C$

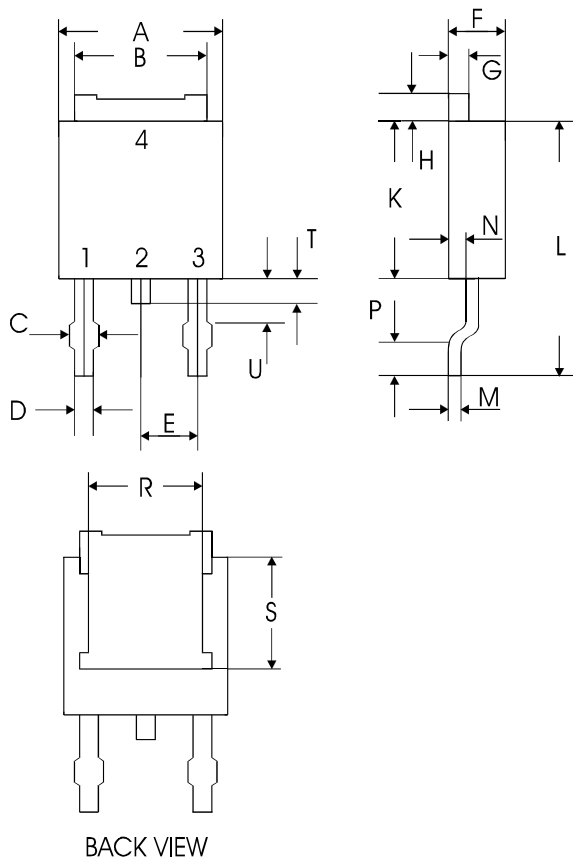


9 Max. transient thermal impedance

$$Z_{thJC} = f(t_p)$$

parameter : $D = t_p/T$





P-T0252 (D-Pak)

symbol	dimensions			
	[mm]		inch	
	min	max	min	max
A	6.40	6.73	0.2520	0.2650
B	5.25	5.50	0.2067	0.2165
C	(0.65)	(1.15)	(0.0256)	(0.0453)
D	0.63	0.89	0.0248	0.0350
E	2.28		0.2520	
F	2.19	2.39	0.0862	0.0941
G	0.76	0.98	0.0299	0.0386
H	0.90	1.21	0.0354	0.0476
K	5.97	6.23	0.2350	0.2453
L	9.40	10.40	0.3701	0.4094
M	0.46	0.58	0.0181	0.0228
N	0.87	1.15	0.0343	0.0453
P	0.51	-	0.0201	-
R	5.00	-	0.1969	-
S	4.17	-	0.1642	-
T	0.26	1.02	0.0102	0.0402
U	-	-	-	-

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